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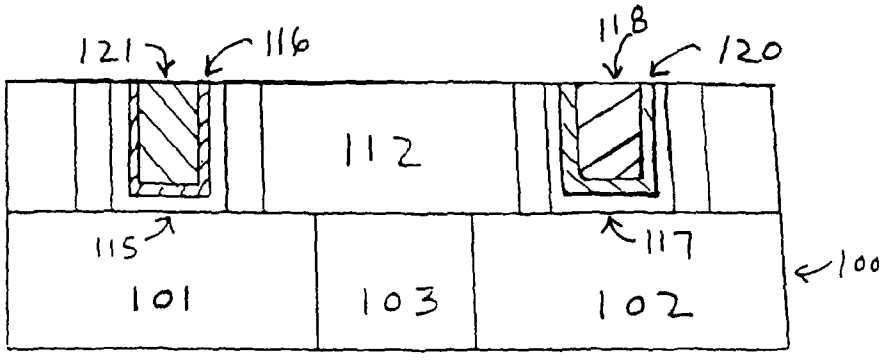
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(54) **Title:** A SEMICONDUCTOR DEVICE WITH A HIGH-K GATE DIELECTRIC AND A METAL GATE ELECTRODE



(57) **Abstract:** A semiconductor device is described that comprises a gate dielectric and a metal gate electrode that comprises an aluminide.

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